# MT3454

### N-Channel 200V Switch MOSFET

### **Features**

- Typ  $R_{DS}(on)=0.60\Omega$  @  $V_{GS}=10V,I_{D}=1.3A$
- · Fast Switching Speed
- · Low Gate Charge
- · High Power and Current Handling Capability
- · ESD Rating:2000V HBM

### **General Description**

This N-Channel MOSFET is produced using MOS-TECH Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet

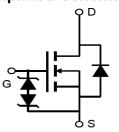
### **Applications**

- DC Switch
- Led Driver

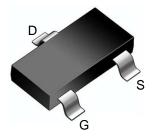


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### **Simplified Schematic**



## MARKING DIAGRAM & PIN ASSIGNMENT



MOSFET Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter			Ratings	Units	
V <sub>DSS</sub>	Drain to Source V	Drain to Source Voltage			200	V
V <sub>GSS</sub>	Gate to Source Vo	Gate to Source Voltage			±20	V
I <sub>D</sub>	Drain Curren - Continuous (Silicon Limited) T <sub>C</sub> = 25°C			1.3		
	- Continuous( Package Limited) T <sub>C</sub> = 25°C			2.0	A	
	- Continuous			T <sub>C</sub> = 25°	3.0	
	- Pulsed			4	Α	
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note			(Note 3)	1.0	mJ
P <sub>D</sub>	Power Dissipation		- T <sub>C</sub> = 25°C	(Note 1a)	2.4	W
			- T <sub>A</sub> = 25°C	(Note 1b)	0.2	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range			-55 to +155	°C	

### **Thermal Characteristics**

Symbol	Parameter		Ratings	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	(Note 1)	5.0	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	52	- 0/00

### **Package Marking and Ordering Information**

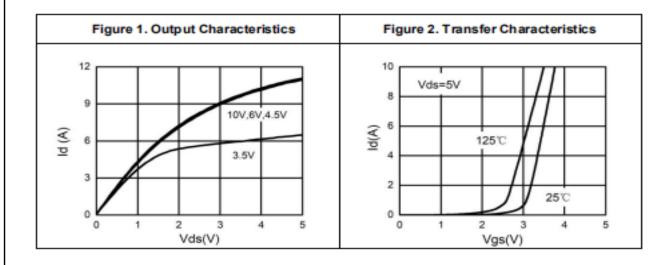
Device Marking	Device	Package	Reel Size	Tape Width	Quantity
MT3454	MT3454	SOT- 23	-	-	3000

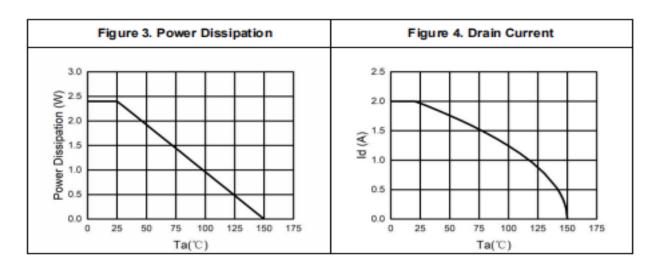
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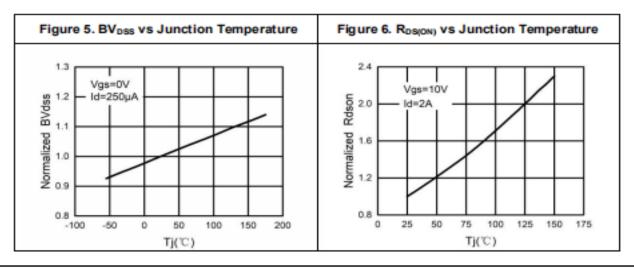
Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Cha	racteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA				V
ΔBV <sub>DSS</sub> / ΔΤ <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		0.09		V/°C
I <sub>DSS</sub>	7 0 1 1/1 5 1 0 1	V <sub>DS</sub> =200V , V <sub>GS</sub> = 0 V			1	μΑ
	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 80 V, T <sub>C</sub> = 125°C			10	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 20 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -20 V, V <sub>DS</sub> = 0 V			-100	nA
On Cha	racteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	1	1.5	3.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V I <sub>D</sub> =1A		0.5	0.65	Ω
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =5V ,   <sub>D</sub> =2A (Note 4)		8.0		s
<b>Dynam</b> i C <sub>iss</sub>	ic Characteristics Input Capacitance	= 1 A			1500	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz			200	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 - 1.0 WH 12			160	pF
Switchi	ng Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time			10		ns
t <sub>r</sub>	Turn-On Rise Time	$V_{GS} = 10V, V_{DS} = 75V$		13		ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$R_L=25\Omega, R_{GEN}=6\Omega$		16		ns
t <sub>f</sub>	Turn-Off Fall Time	The second secon		14		ns
Q <sub>g</sub>	Total Gate Charge	V <sub>GS</sub> =10V, V <sub>DS</sub> =100V, I <sub>D</sub> =2A		16.8		nC
Q <sub>gs</sub>	Gate-Source Charge	VGS-10V, VDS-100V, ID-2A		2.5		nC
Q <sub>gd</sub>	Gate-Drain Charge			6.8		nC
	course Diede Cheresteristics of	nd Maximum Batings		•		•
Drain-S	Source Diode Characteristics and Maximum Ratings  Maximum Continuous Drain-Source Diode Forward Current				1.3	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				1.3	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage $V_{DS}=0V$ , $I_{S}=2A$				1.2	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 2A		80		ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI <sub>F</sub> / dt = 100 A/μs (Note 4)		0.195		μС

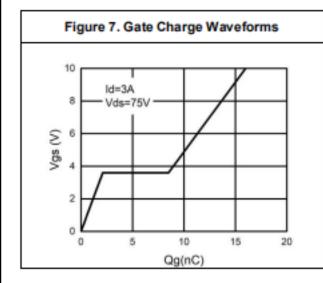
 $<sup>\</sup>label{eq:Notes:1} \textbf{Notes:} \\ \textbf{1. Repetitive Rating: Pulse width limited by maximum junction temperature } \\ \textbf{2. L} = \textbf{1.35mH, } \\ \textbf{I}_{AB} = \textbf{15.6A}, \\ \textbf{V}_{DD} = \textbf{25V}, \\ \textbf{R}_{G} = \textbf{25} \ \Omega, \\ \textbf{Starting } \\ \textbf{T}_{J} = \textbf{25}^{\circ} \textbf{C} \\ \textbf{3. } \\ \textbf{I}_{SD} \leq \textbf{19A}, \\ \textbf{didt} \leq \textbf{300A/\mus}, \\ \textbf{V}_{DD} \leq \textbf{BV}_{DSS}, \\ \textbf{Starting } \\ \textbf{T}_{J} = \textbf{25}^{\circ} \textbf{C} \\ \textbf{4. Pulse Test: Pulse width } \leq \textbf{300\mus}, \\ \textbf{Duty cycle} \leq \textbf{2\%} \\ \textbf{5. Essentially independent of operating temperature} \\ \\ \textbf{6. Essentially independent of operating temperature} \\ \textbf{6. Essentially independent of operating temperature} \\ \textbf{7. Essentially independent of operating temperature} \\ \textbf{8. Essentially independent of operating temperature} \\ \textbf{8.$ 

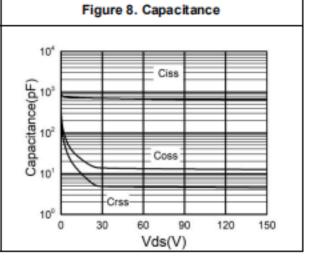
## Typical Electrical And Thermal Characteristics (Curves)

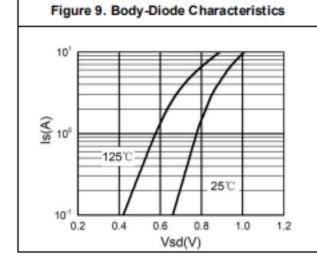


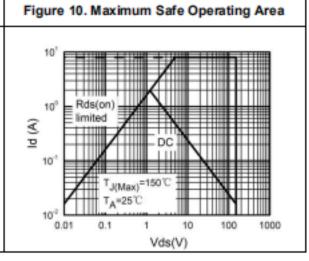












### Test Circuits and Waveforms

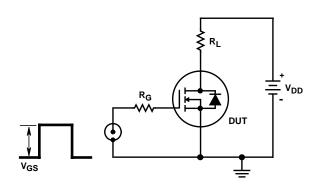


FIGURE 11. SWITCHING TIME TEST CIRCUIT

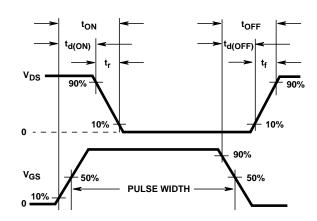


FIGURE 12. RESISTIVE SWITCHING WAVEFORMS

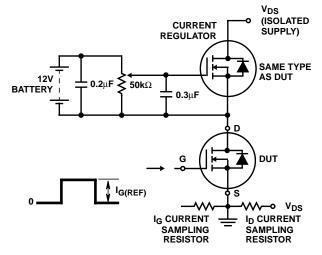


FIGURE 13. GATE CHARGE TEST CIRCUIT

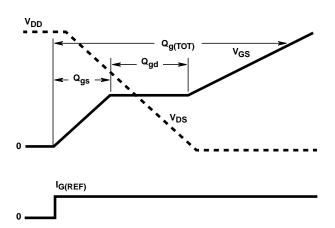
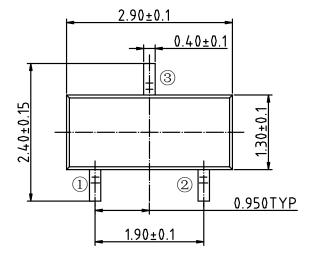
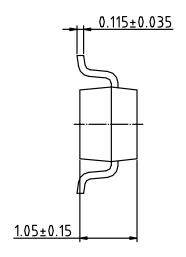


FIGURE 14. GATE CHARGE WAVEFORMS

### Package Information







SOT23 Units:mm

### **SOT-23 Std Tape and Reel Data** SOT23-3L Packaging Configuration: Figure 1.0 Cus tomized Lab el Packaging Description: Packaging Description: SOT23-31 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are a shipped with 3,000 units per 7" or 177mm diameter reel. The reels are dark blue in color and is made of polystyrene plastic (anti-static coated). Other option comes in 10,000 units per 13" or 330cm diameter reel. This and so me other options are described in the Packaging Information table. Antistatic Cover Tape described in the Fackaging information table. These full freels are individually labeled and placed inside as tandard immediate box made of recyclable corrugated brown paper with a Fairchild logo printing. One box contains five reels maximum. And these immediate boxes are placed inside a labeled is hipping box which comes in different sizes depending on the number of parts shipped. ACTR Label E mbosse d Carri er Tape SOT23-3L Packaging Information S tandar d Packaging Option D87Z SOT23-3L Unit Orientation Packaging type TNR TNR Qty per Reel/Tube/Bag 3,000 10,000 Reel Size 7" Dia 13" Box Dimension (mm) 193x 183 x80 355x 333 x 40 Max qty per Box 15,000 30,000 Weight per unit (gm) 0.0082 0.0082 Weight per Reel (kg) 0.1175 0.4006 55 X X MARKING DIAGRAM Note/Comments X: Month code Barcode Lab el X: Year code -55: Part No. Barcode Labels ample XH1 MT3455AACTR QTY: 3000 MOS-TECH SEMICONDUCTOR LTD (ACTR) 193mm x 183m m x 80m m Pizza B ox for S tandard O ption SOT23-3L Tape Leader and Trailer Configuration: Figure 2.0 0 $\circ$ ComponentsCover Tape Trailer Ta pe 300mm minimum or Leade r T ape 500mm minimum or 75 em pty pockets 125 empty pockets

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